

TC40H367P/F

TC40H368P/F

C²MOS DIGITAL INTEGRATED CIRCUIT
SILICON MONOLITHIC

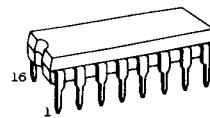
TC40H367 HEX BUS BUFFER NONINVERTED 3-STATE OUTPUT

TC40H368 HEX BUS BUFFER INVERTED 3-STATE OUTPUT

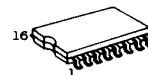
The TC40H367 and the TC40H368 are hex inverting and non-inverting buffers provided with 3-state output functions. Respective DISABLE inputs for putting outputs in disable conditions are of circuit configuration common in two circuits and four circuits. Therefore, these buffers are suitable for controlling 4-bit data lines.

Further, the output current of each buffer is large, permitting direct drive of then LSTTL input lines.

The TC40H367 and the TC40H368 are compatible in function and pin assignment with the TTL 74LS367 and TTL 74LS368. Further, Toshiba's original product, the TC5012BP, is the same as the TC40H367.



DIP16 (3D16A-P)



MFP16 (F16GC-P)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{DD}	V _{SS} -0.5 ~ V _{SS} +10	V
Input Voltage	V _{IN}	V _{SS} -0.5 ~ V _{DD} +0.5	V
Output Voltage	V _{OUT}	V _{SS} -0.5 ~ V _{DD} +0.5	V
Input Current	I _{IN}	±10	mA
Power Dissipation	P _D	300(DIP)/180(MFP)	mW
Storage Temperature	T _{stg}	-65 ~ 150	°C
Lead Temp./Time	T _{sol}	260°C • 10 sec	

TRUTH TABLE

TC40H367P

DISABLE INPUT	INPUT	OUTPUT
L	L	L
L	H	H
H	*	HZ

TC40H368P

DISABLE INPUT	INPUT	OUTPUT
L	L	H
L	H	L
H	*	HZ

HZ = HIGH IMPEDANCE

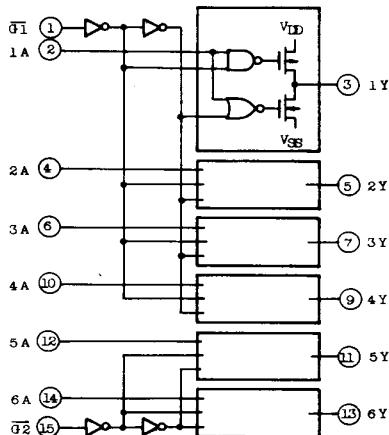
* = Don't care

RECOMMENDED OPERATING CONDITIONS

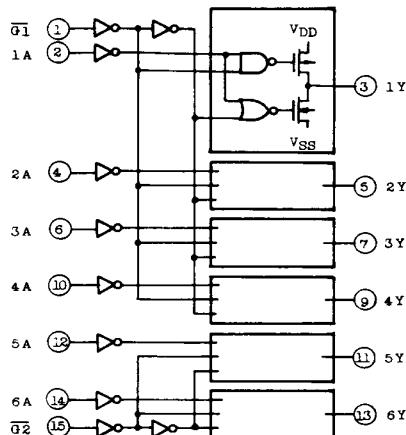
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{DD}		2.0	-	8.0	V
Input Voltage	V _{IN}		0	-	V _{DD}	V
Operating Temperature	T _{opr}		-40	-	85	°C

**TC40H367P/F
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TC40H367



TC40H368



* ALL INPUTS ARE EQUIPPED WITH PROTECTION CIRCUIT.

ELECTRICAL CHARACTERISTICS (V_{SS}=0V)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{DD}	-40°C		25°C			85°C		UNIT
				MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	
High Level Output Voltage	V _{OH}	I _{OUT} <1μA V _{IN} =V _{SS} , V _{DD}	5	4.95	-	4.95	5.0	-	4.95	-	V
Low Level Output Voltage	V _{OL}	I _{OUT} <1μA V _{IN} =V _{SS} , V _{DD}	5	-	0.05	-	0.0	0.05	-	0.05	
High Level Output Current	I _{OH}	V _{OUT} =4.6V V _{IN} =V _{SS} , V _{DD}	5	-0.95	-	-0.88	-	-	-0.8	-	mA
Low Level Output Current	I _{OL}	V _{OUT} =0.4V V _{IN} =V _{SS} , V _{DD}	5	4.7	-	4.4	-	-	4.0	-	mA
Input "H" Level Voltage	V _{IH}	I _{OUT} <1μA V _{OUT} =0.5V	5	4.0	-	4.0	-	-	4.0	-	V
	V _{IL}	V _{OUT} =4.5V	5	-	1.0	-	-	1.0	-	1.0	
Input "H" Level Current	I _{IH}	V _{IN} =8.0V	8	-	0.3	-	10 ⁻⁵	0.3	-	1.0	μA
	I _{IL}	V _{IN} =0.0V	8	-	-0.3	-	-10 ⁻⁵	-0.3	-	-1.0	
Output Disable Current	I _{DH}	V _{DH} =8.0V	8	-	0.5	-	10 ⁻⁴	0.5	-	5	μA
	I _{DL}	V _{DL} =0.0V	8	-	-0.5	-	-10 ⁻⁴	-0.5	-	-5	
Quiescent Supply Current	I _{DD}	*V _{IN} =V _{SS} , V _{DD}	5	-	5.0	-	0.005	5.0	-	25	μA

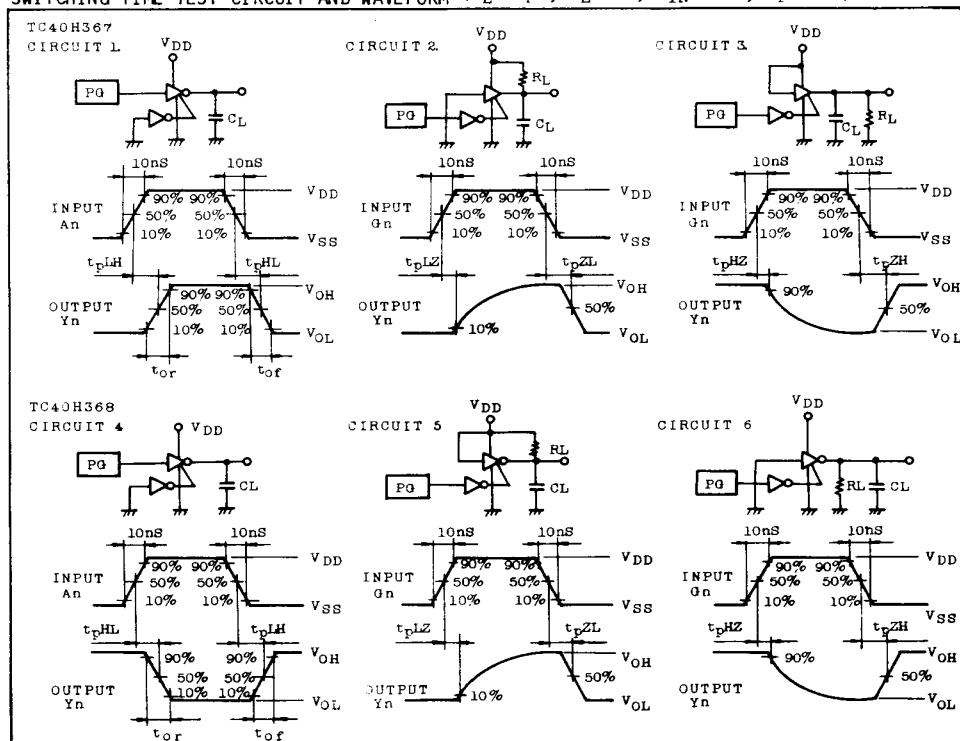
*All Input valid combinations

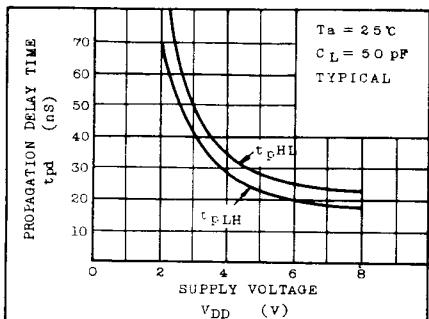
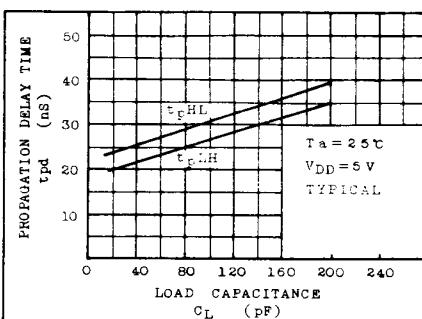
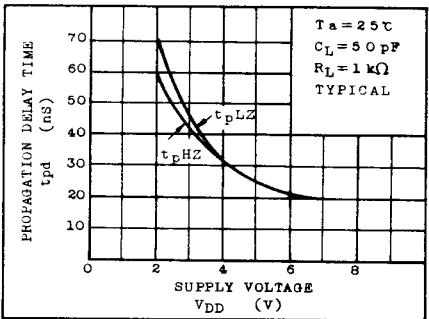
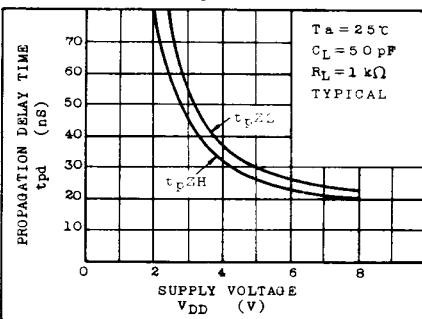
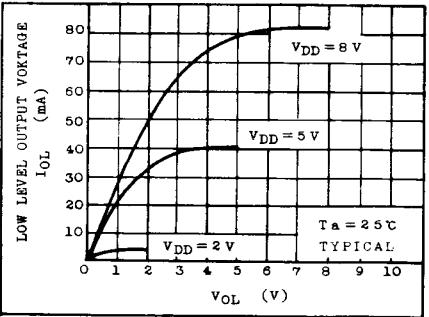
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SWITCHING CHARACTERISTICS ($T_a=25^\circ\text{C}$, $V_{SS}=0\text{V}$, $V_{DD}=5\text{V}$, $C_L=50\text{pF}$, $R_L=1\text{k}\Omega$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	TC40H367			TC40H368			UNIT
				MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Output Rise Time		t_{or}		-	17	35	-	17	35	ns
Output Fall Time		t_{of}	Fig. 1, 4	-	14	30	-	14	30	ns
Propagation Delay Time	High Level	t_{pLH}		-	20	35	-	23	35	ns
	Low Level	t_{pHL}	Fig. 1, 4	-	25	41	-	27	41	ns
Output Disable Time	High Level	t_{pHZ}	Fig. 3, 6	-	26	45	-	26	45	ns
Time	Low Level	t_{pLZ}	Fig. 2, 5	-	26	45	-	26	45	ns
Output Enable Time	High Level	t_{pZH}	Fig. 3, 6	-	26	45	-	26	45	ns
	Low Level	t_{pZL}	Fig. 2, 5	-	30	45	-	30	45	ns
Input Capacitance		C_{IN}		-	5	-	-	5	-	pF
Output Capacitance		C_{OUT}		-	16	-	-	16	-	

SWITCHING TIME TEST CIRCUIT AND WAVEFORM ($C_L=50\text{pF}$, $R_L=1\text{k}\Omega$, $f_{IN}=1\text{MHz}$, $t_f=10\text{ns}$)

TC40H367P/F
TC40H368P/F
 $t_{pd} = V_{DD}$  $t_{pd} = C_L$  $t_{pd} = V_{DD}$  $t_{pd} = V_{DD}$  $I_{OL} = V_{OL}$  $I_{OH} = (V_{DD} - V_{OH})$ 